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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

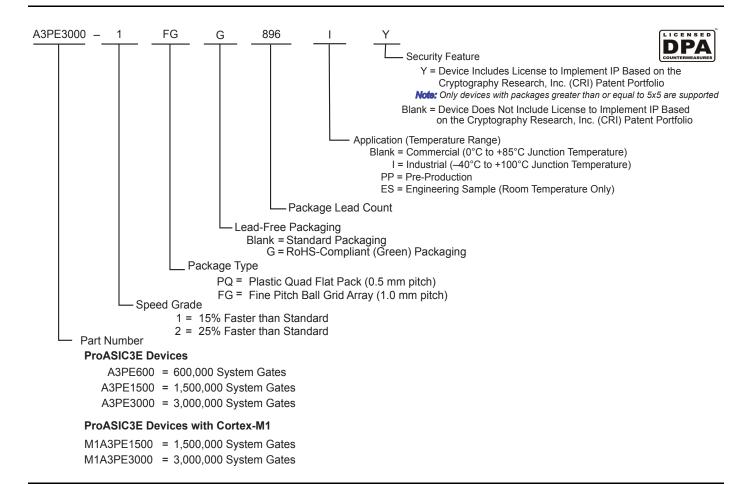
Details

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	147
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-pqg208

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

ProASIC3E Ordering Information





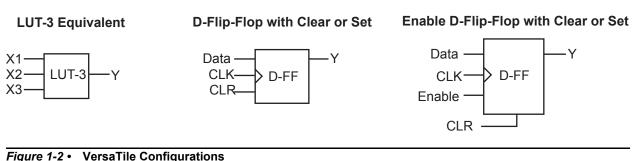
ProASIC3E Device Family Overview

VersaTiles

The ProASIC3E core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS®} core tiles. The ProASIC3E VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-2 for VersaTile configurations.



User Nonvolatile FlashROM

ProASIC3E devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- · Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- · Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard ProASIC3E IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks, as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The ProASIC3E development software solutions, Libero[®] System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.



2 – ProASIC3E DC and Switching Characteristics

General Specifications

DC and switching characteristics for –F speed grade targets are based only on simulation.

The characteristics provided for the –F speed grade are subject to change after establishing FPGA specifications. Some restrictions might be added and will be reflected in future revisions of this document. The –F speed grade is only supported in the commercial temperature range.

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Symbol	Parameter	Limits	Units				
VCC	DC core supply voltage	-0.3 to 1.65					
VJTAG	JTAG DC voltage	-0.3 to 3.75	V				
VPUMP	Programming voltage	-0.3 to 3.75	V				
VCCPLL	Analog power supply (PLL)	-0.3 to 1.65	V				
VCCI ²	DC I/O output buffer supply voltage	-0.3 to 3.75	V				
VMV ²	DC I/O input buffer supply voltage	-0.3 to 3.75	V				
VI	I/O input voltage	 -0.3 V to 3.6 V (when I/O hot insertion mode is enabled) -0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled) 	V				
T _{STG} ³	Storage temperature	-65 to +150	°C				
T _J ³	Junction temperature	+125	°C				

Notes:

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-3 on page 2-2.

 VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.

3. For flash programming and retention maximum limits, refer to Table 2-3 on page 2-2, and for recommended operating limits, refer to Table 2-2 on page 2-2.

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ProASIC3E DC and Switching Characteristics

Symbol	Para	meter	Commercial	Industrial	Units
T _A	Ambient temperature		0 to +70	-40 to +85	°C
TJ	Junction temperature		0 to +85	-40 to +100	°C
VCC	1.5 V DC core supply volta	age	1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode ²	3.15 to 3.45	3.15 to 3.45	V
		Operation ³	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL	_)	1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV ⁴	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.0 V DC supply voltage ⁵		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS dif	fferential I/O	2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Table 2-2 • Recommended Operating Conditions¹

Notes:

1. All parameters representing voltages are measured with respect to GND unless otherwise specified.

2. The programming temperature range supported is $T_{ambient} = 0^{\circ}C$ to $85^{\circ}C$.

3. VPUMP can be left floating during normal operation (not programming mode).

- 4. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-13 on page 2-16. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.
- 5. To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.
- 6. 3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.

Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature¹

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T _{STG} (°C) ²	Maximum Operating Junction Temperature T _J (°C) ²
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.

2. These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.

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ProASIC3E DC and Switching Characteristics

Table 2-9 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings (continued) (continued)¹

	C _{LOAD} (pF)			Dynamic Power PAC10 (µW/MHz) ³	
SSTL3 (I)	30	3.3	26.02	114.87	
SSTL3 (II)	30	3.3	42.21	131.76	
Differential	•				
LVDS/B-LVDS/M-LVDS	-	2.5	7.70	89.62	
LVPECL	-	3.3	19.42	168.02	
Notes:	•		1	1	

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.

2. PDC3 is the static power (where applicable) measured on VCCI.

3. PAC10 is the total dynamic power measured on VCC and VCCI.

4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Power Consumption of Various Internal Resources

Table 2-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices

		Device-Specific Dynamic Contributions (µW/MHz)					
Parameter	Definition	A3PE600	A3PE1500	A3PE3000			
PAC1	Clock contribution of a Global Rib	12.77	16.21	19.7			
PAC2	Clock contribution of a Global Spine	1.85	3.06	4.16			
PAC3	Clock contribution of a VersaTile row		0.88				
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12					
PAC5	First contribution of a VersaTile used as a sequential module	as a sequential 0.07					
PAC6	Second contribution of a VersaTile used as a sequential 0.29 module						
PAC7	Contribution of a VersaTile used as a combinatorial module	0.29					
PAC8	Average contribution of a routing net		0.70				
PAC9	Contribution of an I/O input pin (standard-dependent)	See 7	Table 2-8 on pag	ge 2-6.			
PAC10	Contribution of an I/O output pin (standard-dependent)	See	Table 2-9 on pag	ge 2-7			
PAC11	Average contribution of a RAM block during a read operation		25.00				
PAC12	Average contribution of a RAM block during a write operation		30.00				
PAC13	Static PLL contribution		2.55 mW				
PAC14	Dynamic contribution for PLL		2.60				

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power calculator or SmartPower in Libero SoC.

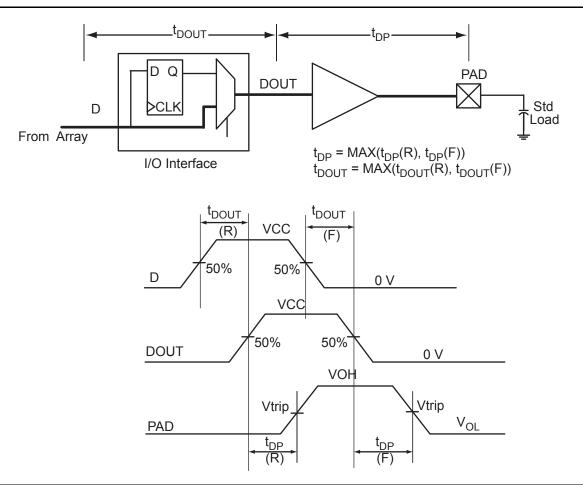


Figure 2-4 • Output Buffer Model and Delays (example)



Detailed I/O DC Characteristics

Table 2-18 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C _{IN}	Input capacitance	VIN = 0, f = 1.0 MHz		8	pF
CINCLK	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz		8	pF

Table 2-19 • I/O Output Buffer Maximum Resistances¹

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTL / 3.3 V LVCMOS	4 mA	100	300
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	4 mA	100	200
Ī	8 mA	50	100
T	12 mA	25	50
	16 mA	20	40
Ī	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75
3.3 V GTL	20 mA ⁴	11	_
2.5 V GTL	20 mA ⁴	14	_

Notes:

- These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.
- 2. R_(PULL-DOWN-MAX) = (VOLspec) / IOLspec
- 3. R_(PULL-UP-MAX) = (VCCImax VOHspec) / IOHspec
- 4. Output drive strength is below JEDEC specification.

3.3 V LVCMOS Wide Range

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive	v	IL	v	н	VOL	VOH	IOL	юн	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	109	103	10	10
100 µA	16 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	127	132	10	10
100 µA	24 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	181	268	10	10

Table 2-29 • Minimum and Maximum DC Input and Output Levels

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.

4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

5. Currents are measured at 85°C junction temperature.

6. Software default selection highlighted in gray.

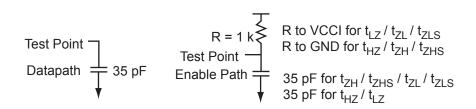


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	1.4	_	35

Note: **Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

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ProASIC3E DC and Switching Characteristics

2.5 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-57 • Minimum and Maximum DC Input and Output Levels

2.5 V GTL+		VIL	VIH		VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA²	μA²
33 mA	-0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	-	33	33	124	169	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

2. Currents are measured at 85°C junction temperature.

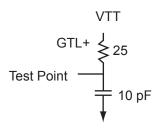


Figure 2-15 • AC Loading

Table 2-58 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-59 • 2.5 V GTL+

```
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.0 V
```

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.60	2.21	0.04	1.51	0.43	2.25	2.10			4.48	4.34	ns
–1	0.51	1.88	0.04	1.29	0.36	1.91	1.79			3.81	3.69	ns
-2	0.45	1.65	0.03	1.13	0.32	1.68	1.57			3.35	3.24	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

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ProASIC3E DC and Switching Characteristics

SSTL3 Class II

Stub-Speed Terminated Logic for 3.3 V memory bus standard (JESD8-8). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-75 • Minimum and Maximum DC Input and Output Levels

SSTL3 Class II		VIL	VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA²	μA²
21 mA	-0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21	109	103	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

2. Currents are measured at 85°C junction temperature.

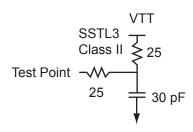


Figure 2-21 • AC Loading

Table 2-76 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.5	1.5	1.485	30

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

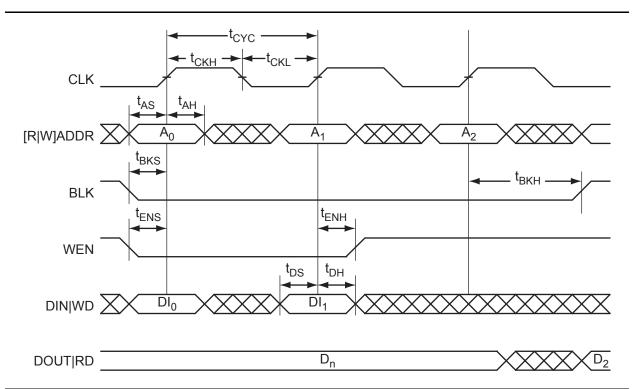
Table 2-77 • SSTL3 Class II

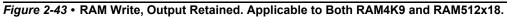
```
Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V, VREF = 1.5 V
```

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.66	2.07	0.04	1.25	0.43	2.10	1.67			4.34	3.91	ns
-1	0.56	1.76	0.04	1.06	0.36	1.79	1.42			3.69	3.32	ns
-2	0.49	1.54	0.03	0.93	0.32	1.57	1.25			3.24	2.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Wicrosemi. ProASIC3E DC and Switching Characteristics





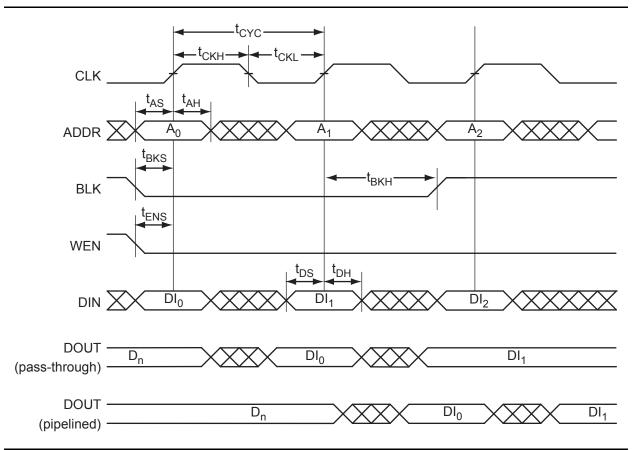


Figure 2-44 • RAM Write, Output as Write Data. Applicable to RAM4K9 Only.

Refer to the I/O Structure section of the *ProASIC3E FPGA Fabric User's Guide* for an explanation of the naming of global pins.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pullup/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 W to 1 k Ω will satisfy the requirements. Refer to Table 3-1 for more information.

VJTAG	Tie-Off Resistance
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 kΩ

Table 3-1 • Recommended Tie-Off Values for the TCK and TRST Pins

Notes:

- 1. Equivalent parallel resistance if more than one device is on the JTAG chain
- 2. The TCK pin can be pulled up/down.
- 3. The TRST pin is pulled down.

TDI

TMS

Test Data Input

Test Data Output

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 3-1 and must satisfy the parallel resistance value requirement. The values in Table 3-1 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements.



Pin Descriptions and Packaging

Special Function Pins

NC

No Connect

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC

Do Not Connect

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

User's Guides

ProASIC3E FPGA Fabric User's Guide

http://www.microsemi.com/document-portal/doc_download/130883-proasic3e-fpga-fabric-user-s-guide

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

http://www.microsemi.com/document-portal/doc_download/131095-package-mechanical-drawings

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials: http://www.microsemi.com/products/fpga-soc/solutions.



	PQ208		PQ208		PQ208		
Pin Number	A3PE600 Function	Pin Number	A3PE600 Function	Pin Number	A3PE600 Function		
108	TDO	144	IO47PDB2V1	180	IO19NPB0V2		
109	TRST	145	IO44NDB2V1	181	IO18NPB0V2		
110	VJTAG	146	IO44PDB2V1	182	IO17PPB0V2		
111	VMV3	147	IO43NDB2V0	183	IO16PPB0V2		
112	GDA0/IO67NPB3V1	148	IO43PDB2V0	184	IO17NPB0V2		
113	GDB0/IO66NPB3V1	149	IO40NDB2V0	185	IO16NPB0V2		
114	GDA1/IO67PPB3V1	150	IO40PDB2V0	186	VCCIB0		
115	GDB1/IO66PPB3V1	151	GBC2/IO38PSB2V0	187	VCC		
116	GDC0/IO65NDB3V1	152	GBA2/IO36PSB2V0	188	IO15PDB0V2		
117	GDC1/IO65PDB3V1	153	GBB2/IO37PSB2V0	189	IO15NDB0V2		
118	IO62NDB3V1	154	VMV2	190	IO13PDB0V2		
119	IO62PDB3V1	155	GNDQ	191	IO13NDB0V2		
120	IO58NDB3V0	156	GND	192	IO11PSB0V1		
121	IO58PDB3V0	157	VMV1	193	IO09PDB0V1		
122	GND	158	GNDQ	194	IO09NDB0V1		
123	VCCIB3	159	GBA1/IO35PDB1V1	195	GND		
124	GCC2/IO55PSB3V0	160	GBA0/IO35NDB1V1	196	IO07PDB0V1		
125	GCB2/IO54PSB3V0	161	GBB1/IO34PDB1V1	197	IO07NDB0V1		
126	NC	162	GND	198	IO05PDB0V0		
127	IO53NDB3V0	163	GBB0/IO34NDB1V1	199	IO05NDB0V0		
128	GCA2/IO53PDB3V0	164	GBC1/IO33PDB1V1	200	VCCIB0		
129	GCA1/IO52PPB3V0	165	GBC0/IO33NDB1V1	201	GAC1/IO02PDB0V0		
130	GND	166	IO31PDB1V1	202	GAC0/IO02NDB0V0		
131	VCCPLC	167	IO31NDB1V1	203	GAB1/IO01PDB0V0		
132	GCA0/IO52NPB3V0	168	IO27PDB1V0	204	GAB0/IO01NDB0V0		
133	VCOMPLC	169	IO27NDB1V0	205	GAA1/IO00PDB0V0		
134	GCB0/IO51NDB2V1	170	VCCIB1	206	GAA0/IO00NDB0V0		
135	GCB1/IO51PDB2V1	171	VCC	207	GNDQ		
136	GCC1/IO50PSB2V1	172	IO23PPB1V0	208	VMV0		
137	IO49NDB2V1	173	IO22PSB1V0				
138	IO49PDB2V1	174	IO23NPB1V0				
139	IO48PSB2V1	175	IO21PDB1V0				
140	VCCIB2	176	IO21NDB1V0				
141	GND	177	IO19PPB0V2				
142	VCC	178	GND				
143	IO47NDB2V1	179	IO18PPB0V2				



Package Pin Assignments

	PQ208		PQ208		PQ208
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
1	GND	40	VCCIB6	79	IO194NDB5V0
2	GNDQ	41	GND	80	IO194PDB5V0
3	VMV7	42	IO244PDB6V1	81	GND
4	GAB2/IO308PSB7V4	43	IO244NDB6V1	82	IO184NDB4V3
5	GAA2/IO309PDB7V4	44	GEC1/IO236PDB6V0	83	IO184PDB4V3
6	IO309NDB7V4	45	GEC0/IO236NDB6V0	84	IO180NDB4V3
7	GAC2/IO307PDB7V4	46	GEB1/IO235PPB6V0	85	IO180PDB4V3
8	IO307NDB7V4	47	GEA1/IO234PPB6V0	86	IO176NDB4V2
9	IO303PDB7V3	48	GEB0/IO235NPB6V0	87	IO176PDB4V2
10	IO303NDB7V3	49	GEA0/IO234NPB6V0	88	VCC
11	IO299PDB7V3	50	VMV6	89	VCCIB4
12	IO299NDB7V3	51	GNDQ	90	IO170NDB4V2
13	IO295PDB7V2	52	GND	91	IO170PDB4V2
14	IO295NDB7V2	53	VMV5	92	IO166NDB4V1
15	IO291PSB7V2	54	GNDQ	93	IO166PDB4V1
16	VCC	55	IO233NDB5V4	94	IO156NDB4V0
17	GND	56	GEA2/IO233PDB5V4	95	GDC2/IO156PDB4V0
18	VCCIB7	57	IO232NDB5V4	96	IO154NPB4V0
19	IO285PDB7V1	58	GEB2/IO232PDB5V4	97	GND
20	IO285NDB7V1	59	IO231NDB5V4	98	GDB2/IO155PSB4V0
21	IO279PSB7V0	60	GEC2/IO231PDB5V4	99	GDA2/IO154PPB4V0
22	GFC1/IO275PSB7V0	61	IO230PSB5V4	100	GNDQ
23	GFB1/IO274PDB7V0	62	VCCIB5	101	ТСК
24	GFB0/IO274NDB7V0	63	IO218NDB5V3	102	TDI
25	VCOMPLF	64	IO218PDB5V3	103	TMS
26	GFA0/IO273NPB6V4	65	GND	104	VMV4
27	VCCPLF	66	IO214PSB5V2	105	GND
28	GFA1/IO273PPB6V4	67	IO212NDB5V2	106	VPUMP
29	GND	68	IO212PDB5V2	107	GNDQ
30	GFA2/IO272PDB6V4	69	IO208NDB5V1	108	TDO
31	IO272NDB6V4	70	IO208PDB5V1	109	TRST
32	GFB2/IO271PPB6V4	71	VCC	110	VJTAG
33	GFC2/IO270PPB6V4	72	VCCIB5	111	VMV3
34	IO271NPB6V4	73	IO202NDB5V1	112	GDA0/IO153NPB3V4
35	IO270NPB6V4	74	IO202PDB5V1	113	GDB0/IO152NPB3V4
36	VCC	75	IO198NDB5V0	114	GDA1/IO153PPB3V4
37	IO252PDB6V2	76	IO198PDB5V0	115	GDB1/IO152PPB3V4
38	IO252NDB6V2	77	IO197NDB5V0	116	GDC0/IO151NDB3V4
39	IO248PSB6V1	78	IO197PDB5V0	117	GDC1/IO151PDB3V4

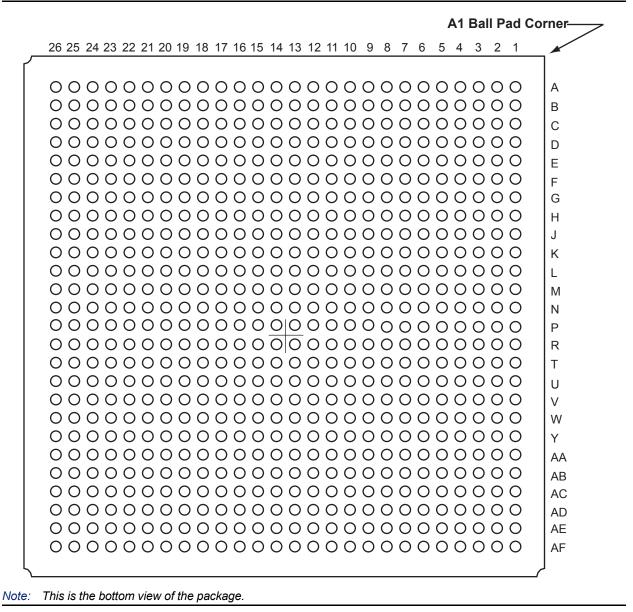


Package Pin Assignments

	FG256		FG256		FG256
Pin Number	A3PE600 Function	Pin Number	A3PE600 Function	Pin Number	A3PE600 Function
G13	GCC1/IO50PPB2V1	K1	GFC2/IO115PSB6V1	M5	VMV5
G14	IO44NDB2V1	K2	IO113PPB6V1	M6	VCCIB5
G15	IO44PDB2V1	K3	IO112PDB6V1	M7	VCCIB5
G16	IO49NSB2V1	K4	IO112NDB6V1	M8	IO84NDB5V0
H1	GFB0/IO119NPB7V0	K5	VCCIB6	M9	IO84PDB5V0
H2	GFA0/IO118NDB6V1	K6	VCC	M10	VCCIB4
H3	GFB1/IO119PPB7V0	K7	GND	M11	VCCIB4
H4	VCOMPLF	K8	GND	M12	VMV3
H5	GFC0/IO120NPB7V0	K9	GND	M13	VCCPLD
H6	VCC	K10	GND	M14	GDB1/IO66PPB3V1
H7	GND	K11	VCC	M15	GDC1/IO65PDB3V1
H8	GND	K12	VCCIB3	M16	IO61NDB3V1
H9	GND	K13	IO54NPB3V0	N1	IO105PDB6V0
H10	GND	K14	IO57NPB3V0	N2	IO105NDB6V0
H11	VCC	K15	IO55NPB3V0	N3	GEC1/IO104PPB6V0
H12	GCC0/IO50NPB2V1	K16	IO57PPB3V0	N4	VCOMPLE
H13	GCB1/IO51PPB2V1	L1	IO113NPB6V1	N5	GNDQ
H14	GCA0/IO52NPB3V0	L2	IO109PPB6V0	N6	GEA2/IO101PPB5V2
H15	VCOMPLC	L3	IO108PDB6V0	N7	IO92NDB5V1
H16	GCB0/IO51NPB2V1	L4	IO108NDB6V0	N8	IO90NDB5V1
J1	GFA2/IO117PSB6V1	L5	VCCIB6	N9	IO82NDB5V0
J2	GFA1/IO118PDB6V1	L6	GND	N10	IO74NDB4V1
J3	VCCPLF	L7	VCC	N11	IO74PDB4V1
J4	IO116NDB6V1	L8	VCC	N12	GNDQ
J5	GFB2/IO116PDB6V1	L9	VCC	N13	VCOMPLD
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO65NDB3V1
J8	GND	L12	VCCIB3	N16	GDA1/IO67PDB3V1
J9	GND	L13	GDB0/IO66NPB3V1	P1	GEB1/IO103PDB6V0
J10	GND	L14	IO60NDB3V1	P2	GEB0/IO103NDB6V0
J11	VCC	L15	IO60PDB3V1	P3	VMV6
J12	GCB2/IO54PPB3V0	L16	IO61PDB3V1	P4	VCCPLE
J13	GCA1/IO52PPB3V0	M1	IO109NPB6V0	P5	IO101NPB5V2
J14	GCC2/IO55PPB3V0	M2	IO106NDB6V0	P6	IO95PPB5V1
J15	VCCPLC	M3	IO106PDB6V0	P7	IO92PDB5V1
J16	GCA2/IO53PSB3V0	M4	GEC0/IO104NPB6V0	P8	IO90PDB5V1



FG676



Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.



	FG676
Pin Number	A3PE1500 Function
W25	IO96PDB3V1
W26	IO94NDB3V0
Y1	IO175NDB6V1
Y2	IO175PDB6V1
Y3	IO173NDB6V0
Y4	IO173PDB6V0
Y5	GEC1/IO169PPB6V0
Y6	GNDQ
Y7	VMV6
Y8	VCCIB5
Y9	IO163NDB5V3
Y10	IO159PDB5V3
Y11	IO153PDB5V2
Y12	IO147PDB5V1
Y13	IO139PDB5V0
Y14	IO137PDB5V0
Y15	IO125NDB4V1
Y16	IO125PDB4V1
Y17	IO115NDB4V0
Y18	IO115PDB4V0
Y19	VCC
Y20	VPUMP
Y21	VCOMPLD
Y22	VCCPLD
Y23	IO100NDB3V1
Y24	IO100PDB3V1
Y25	IO96NDB3V1
Y26	IO98PDB3V1



	FG896		FG896		FG896
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
AG9	IO225NPB5V3	AH15	IO195NDB5V0	AJ21	IO173PDB4V2
AG10	IO223NPB5V3	AH16	IO185NDB4V3	AJ22	IO163NDB4V1
AG11	IO221PDB5V3	AH17	IO185PDB4V3	AJ23	IO163PDB4V1
AG12	IO221NDB5V3	AH18	IO181PDB4V3	AJ24	IO167NPB4V1
AG13	IO205NPB5V1	AH19	IO177NDB4V2	AJ25	VCC
AG14	IO199NDB5V0	AH20	IO171NPB4V2	AJ26	IO156NPB4V0
AG15	IO199PDB5V0	AH21	IO165PPB4V1	AJ27	VCC
AG16	IO187NDB4V4	AH22	IO161PPB4V0	AJ28	TMS
AG17	IO187PDB4V4	AH23	IO157NDB4V0	AJ29	GND
AG18	IO181NDB4V3	AH24	IO157PDB4V0	AJ30	GND
AG19	IO171PPB4V2	AH25	IO155NDB4V0	AK2	GND
AG20	IO165NPB4V1	AH26	VCCIB4	AK3	GND
AG21	IO161NPB4V0	AH27	TDI	AK4	IO217PPB5V2
AG22	IO159NDB4V0	AH28	VCC	AK5	GND
AG23	IO159PDB4V0	AH29	VPUMP	AK6	IO215PPB5V2
AG24	IO158PPB4V0	AH30	GND	AK7	GND
AG25	GDB2/IO155PDB4V0	AJ1	GND	AK8	IO207NDB5V1
AG26	GDA2/IO154PPB4V0	AJ2	GND	AK9	IO207PDB5V1
AG27	GND	AJ3	GEA2/IO233PPB5V4	AK10	IO201NDB5V0
AG28	VJTAG	AJ4	VCC	AK11	IO201PDB5V0
AG29	VCC	AJ5	IO217NPB5V2	AK12	IO193NDB4V4
AG30	IO149NDB3V4	AJ6	VCC	AK13	IO193PDB4V4
AH1	GND	AJ7	IO215NPB5V2	AK14	IO197PDB5V0
AH2	IO233NPB5V4	AJ8	IO213NDB5V2	AK15	IO191NDB4V4
AH3	VCC	AJ9	IO213PDB5V2	AK16	IO191PDB4V4
AH4	GEB2/IO232PPB5V4	AJ10	IO209NDB5V1	AK17	IO189NDB4V4
AH5	VCCIB5	AJ11	IO209PDB5V1	AK18	IO189PDB4V4
AH6	IO219NDB5V3	AJ12	IO203NDB5V1	AK19	IO179PPB4V3
AH7	IO219PDB5V3	AJ13	IO203PDB5V1	AK20	IO175NDB4V2
AH8	IO227NDB5V4	AJ14	IO197NDB5V0	AK21	IO175PDB4V2
AH9	IO227PDB5V4	AJ15	IO195PDB5V0	AK22	IO169NDB4V1
AH10	IO225PPB5V3	AJ16	IO183NDB4V3	AK23	IO169PDB4V1
AH11	IO223PPB5V3	AJ17	IO183PDB4V3	AK24	GND
AH12	IO211NDB5V2	AJ18	IO179NPB4V3	AK25	IO167PPB4V1
AH13	IO211PDB5V2	AJ19	IO177PDB4V2	AK26	GND
AH14	IO205PPB5V1	AJ20	IO173NDB4V2	AK27	GDC2/IO156PPB4V0



Revision	Changes	Page				
Revision 9 (Aug 2009)	All references to speed grade –F have been removed from this document.	N/A				
Product Brief v1.2						
	The "Pro I/Os with Advanced I/O Standards" section was revised to add definitions of hot-swap and cold-sparing.	1-6				
DC and Switching Characteristics v1.3	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A				
	IIL and IIH input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.					
	-F was removed from the datasheet. The speed grade is no longer supported.	N/A				
	In the Table 2-2 • Recommended Operating Conditions ¹ "3.0 V DC supply voltage" and note 4 are new.					
	The Table 2-4 • Overshoot and Undershoot Limits ¹ table was updated.					
	The Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays table was updated.					
	There are new parameters and data was updated in the Table 2-99 • RAM4K9 table.					
	There are new parameters and data was updated in the Table 2-100 • RAM512X18 table.	2-77				
Revision 8 (Feb 2008)	Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions is new.	1-II				
Product Brief v1.1						
Revision 7 (Jun 2008) DC and Switching Characteristics v1.2	The title of Table 2-4 • Overshoot and Undershoot Limits ¹ was modified to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3				
	Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels was updated.					
Revision 6 (Jun 2008)	The A3PE600 "FG484" table was missing G22. The pin and its function were added to the table.	4-27				
Revision 5 (Jun 2008) Packaging v1.4	The naming conventions changed for the following pins in the "FG484" for the A3PE600:	4-22				
	Pin Number New Function Name					
	J19 IO45PPB2V1					
	K20 IO45NPB2V1					
	M2 IO114NPB6V1					
	N1 IO114PPB6V1					
	N4 GFC2/IO115PPB6V1					
	P3 IO115NPB6V1					
Revision 4 (Apr 2008) Product Brief v1.0	The product brief portion of the datasheet was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A				
Packaging v1.3	The "FG324" package diagram was replaced.	4-12				